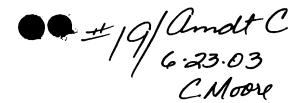


DOCKET NO.: 210313US2SRD



IN THE UNITED STATES PATENT & TRADEMARK OFFICE

IN RE APPLICATION OF

AKIRA NISHIYAMA, ET AL.

: EXAMINER: MAI, A.

SERIAL NO: 09/891,129

RCE FILED:

HEREWITH

: GROUP ART UNIT: 2814

FOR:

SEMICONDUCTOR DEVICE

HAVING AN INSULATING FILM MADE OF A HIGHLY DIELECTRIC THIN FILM AND METHOD OF MANUFACTURING THE SAME

AMENDMENT FILED CONCURRENTLY WITH

REQUEST FOR CONTINUED EXAMINATION (RCE)

COMMISSIONER FOR PATENTS ALEXANDRIA, VIRGINIA 22313

SIR:

Prior to a further examination on the merits, please amend the above-identified application as follows:

IN THE CLAIMS

Please amend claims 1 and 16 to read as follows:¹

1. (Twice Amended) A semiconductor device comprising:

a semiconductor substrate, and

a circuit element using an insulating film formed on said semiconductor substrate.

said insulating film containing a silicon compound containing oxygen, and a metal

compound containing a metal other than silicon and oxygen, said insulating film further

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